

L Number	Hits	Search Text	DB	Time stamp
1	11	"5550435"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 11:31
2	2	("5550435").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 12:25
3	0	extraction adj electrode and field adj emission.ti,ab,clm. and hot adj electron near12 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 12:27
4	2	hot adj electron near15 gate near12 drain near15 (shape or wide or wider) and (mosfet or mos or nmos or nmosfet or pmos or pmosfet or cmos or cmosfet or field adj effect adj transistor or FET).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 12:32
5	54	(US-6031322-\$ or US-6031250-\$ or US-6340962-\$ or US-5214346-\$ or US-5910701-\$ or US-5864147-\$ or US-5142184-\$ or US-5055077-\$ or US-5012482-\$ or US-5191217-\$ or US-5229331-\$ or US-5633560-\$ or US-5347292-\$ or US-6140687-\$ or US-5898198-\$ or US-4968639-\$ or US-5965921-\$ or US-5319233-\$ or US-5285079-\$ or US-5233215-\$ or US-5396096-\$ or US-6028322-\$ or US-5965898-\$ or US-5847408-\$ or US-6369496-\$ or US-6369505-\$).did. or (US-6356014-\$ or US-6351059-\$ or US-6211608-\$ or US-6181060-\$ or US-6075315-\$ or US-5007873-\$ or US-5918137-\$ or US-5844252-\$ or US-5461242-\$ or US-4742380-\$ or US-5550426-\$ or US-6340859-\$ or US-6218771-\$ or US-6084341-\$ or US-6140701-\$ or US-6020595-\$ or US-5920296-\$ or US-5500572-\$ or US-5212426-\$).did. or (JP-09063467-\$ or JP-10074473-\$ or JP-11102637-\$ or JP-01061953-\$ or JP-62229880-\$ or JP-09063466-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.	USPAT; JPO; DERWENT	2003/05/04 13:03

6	4	((US-6031322-\$ or US-6031250-\$ or US-6340962-\$ or US-5214346-\$ or US-5910701-\$ or US-5864147-\$ or US-5142184-\$ or US-5055077-\$ or US-5012482-\$ or US-5191217-\$ or US-5229331-\$ or US-5633560-\$ or US-5347292-\$ or US-6140687-\$ or US-5898198-\$ or US-4968639-\$ or US-5965921-\$ or US-5319233-\$ or US-5285079-\$ or US-5233215-\$ or US-5396096-\$ or US-6028322-\$ or US-5965898-\$ or US-5847408-\$ or US-6369496-\$ or US-6369505-\$).did. or (US-6356014-\$ or US-6351059-\$ or US-6211608-\$ or US-6181060-\$ or US-6075315-\$ or US-5007873-\$ or US-5918137-\$ or US-5844252-\$ or US-5461242-\$ or US-4742380-\$ or US-5550426-\$ or US-6340859-\$ or US-6218771-\$ or US-6084341-\$ or US-6140701-\$ or US-6020595-\$ or US-5920296-\$ or US-5500572-\$ or US-5212426-\$).did. or (JP-09063467-\$ or JP-10074473-\$ or JP-11102637-\$ or JP-01061953-\$ or JP-62229880-\$ or JP-09063466-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.) and hirano.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 13:23
7	224	((shield or shielding) near2 electrode) nearl2 gate and (mosfet or mos or nmos or pmos or cmos or nmosfet or ldmos or ldmosfet or dmos or dmosfet or pmosfet or field adj effect adj transistor).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 13:34
8	0	((shield or shielding) near2 electrode) nearl2 gate and (mosfet or mos or nmos or pmos or cmos or nmosfet or ldmos or ldmosfet or dmos or dmosfet or pmosfet or field adj effect adj transistor).ti,ab,clm. and extraction adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 13:35
9	2	((shield or shielding) near2 electrode) nearl2 gate and (mosfet or mos or nmos or pmos or cmos or nmosfet or ldmos or ldmosfet or dmos or dmosfet or pmosfet or field adj effect adj transistor).ti,ab,clm. and field adj emission adj2 (device or cathode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 13:39
10	2	((shield or shielding) near2 electrode) nearl2 gate and (mosfet or mos or nmos or pmos or cmos or nmosfet or ldmos or ldmosfet or dmos or dmosfet or pmosfet or field adj effect adj transistor).ti,ab,clm. and field adj emission	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 13:44
11	63	((shield or shielding) near2 electrode) nearl2 gate nearl5 substrate and (mosfet or mos or nmos or pmos or cmos or nmosfet or ldmos or ldmosfet or dmos or dmosfet or pmosfet or field adj effect adj transistor).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 13:45
12	14	((shield or shielding) near2 electrode) nearl2 gate nearl5 substrate nearl5 potential and (mosfet or mos or nmos or pmos or cmos or nmosfet or ldmos or ldmosfet or dmos or dmosfet or pmosfet or field adj effect adj transistor).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 13:46

13	14	(US-5633524-\$ or US-5841185-\$ or US-5891765-\$ or US-6201275-\$ or US-6323527-\$ or US-6479330-\$ or US-6531993-\$).did. or (US-20010000922-\$ or US-20010000412-\$ or US-20030027384-\$ or US-20020009837-\$).did. or (JP-60124872-\$).did. or (JP-08181201-\$ or JP-11243199-\$).did.	USPAT; US-PGPUB; JPO; DERWENT	2003/05/04 14:45
14	0	koga.in. and ((US-5633524-\$ or US-5841185-\$ or US-5891765-\$ or US-6201275-\$ or US-6323527-\$ or US-6479330-\$ or US-6531993-\$).did. or (US-20010000922-\$ or US-20010000412-\$ or US-20030027384-\$ or US-20020009837-\$).did. or (JP-60124872-\$).did. or (JP-08181201-\$ or JP-11243199-\$).did.)	USPAT; US-PGPUB; JPO; DERWENT	2003/05/04 14:57
15	2	field adj emission near2 (apparatus or device or cathode).ti,ab,clm. and (symmetry or symmetrical or circular or annular) near12 gate near12 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 15:02
16	4	field adj emission near2 (apparatus or device or cathode).ti,ab,clm. and (symmetry or symmetrical or circular or annular or surround or cylindrical or radial) near12 gate near12 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 17:20
17	4130	((257/10) or (257/249) or (257/401) or (315/167) or (315/169.1) or (315/169.2) or (315/309) or (313/336)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 17:21
19	21	((257/10) or (257/249) or (257/401) or (315/167) or (315/169.1) or (315/169.2) or (315/309) or (313/336)).CCLS.) and gate near12 drain near12 (symmetry or symmetric or symmetrical or cylindric or cylindrical or concentric or concentric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 17:56
20	6	shimomura.in. and ring near3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 18:27
21	3	(ring adj gate or ring-gate) near12 symmetr\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/04 18:09
-	0	jp-963467\$-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/25 08:41
-	0	jp-40963467\$-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 18:10
-	0	"9-63467"	JPO	2002/05/18 20:58
-	0	"963467"	JPO	2002/05/18 20:58
-	0	"963467"\$3	JPO	2002/05/18 20:58
-	4	cold adj electron adj emitting adj element and hirano.in. and ito.in.	JPO	2002/05/18 22:06
-	57881	yamaguchi.in. hirakawa.in. and tomita.in.	JPO	2002/05/18 21:02
-	1	yamaguchi.in. and hirakawa.in. and tomita.in.	JPO	2002/05/18 21:05

-	1	mosfet adj type adj electron adj emission adj element	JPO	2002/05/18 21:06
-	1	jp-07130281\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB JPO	2002/05/18 21:36
-	7109	315/\$6.ccls.	JPO	2002/05/18 22:07
-	52381	315/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/05/18 22:07
-	1832	field adj emission adj cathode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 11:29
-	25	field adj emission adj cathode and gate and (field adj effect adj transistor or fet) and source and drain and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 11:39
-	174	(cold adj cathode or field adj emission adj cathode) and 257/\$7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 11:53
-	135	(cold adj cathode or field adj emission adj cathode and extraction adj gate) and 257/\$7.ccls.	USPAT	2002/05/19 11:53
-	135	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel) and 257/\$7.ccls.	USPAT	2002/05/19 12:04
-	0	cold adj cathode and field adj emission adj (display or cathode) and extraction adj gate and channel and 257/\$7.ccls.	USPAT	2002/05/19 11:59
-	1046	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel) and 313/\$7.ccls.	USPAT	2002/05/19 12:05
-	1045	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel and silicon adj substrate) and 313/\$7.ccls.	USPAT	2002/05/19 12:06
-	1045	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet)) and 313/\$7.ccls.	USPAT	2002/05/19 12:27
-	634	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet)) and 315/\$7.ccls.	USPAT	2002/05/19 12:28
-	1	(cold adj cathode or field adj emission adj cathode) and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet) and 315/\$7.ccls.	USPAT	2002/05/19 12:28
-	0	(cold adj cathode or field adj emission adj cathode) and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet) and 313/\$7.ccls.	USPAT	2002/05/19 12:29
-	1	(cold adj cathode or field adj emission adj cathode) and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet) and (313/\$7.ccls. or 315/\$6.ccls. or 257/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:30

-	34	(US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.	USPAT; JPO; DERWENT	2002/05/19 12:40
-	14	((US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.) and (p-type or p adj type or p-silicon or p-doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:37
-	2	((US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.) and (p-type or p adj type or p-silicon or p-doped)) and source and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:37

-	8	((US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.) and focus\$4	USPAT; JPO; DERWENT	2002/05/19 12:43
-	2	((US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.) and focus\$4 and second near4 gate	USPAT; JPO; DERWENT	2002/05/19 12:45
-	0	cold adj cathode and (fet or field adj effect adj transistor) and field adj emission and extract\$3 near4 gate and source and drain and channel and silicon near4 substrate and (ldd or lightly-doped or lightly adj doped)	USPAT; JPO; DERWENT	2002/05/19 12:48
-	0	cold adj cathode and (fet or field adj effect adj transistor) and field adj emission and extract\$3 near4 gate and source and drain and channel and silicon near4 substrate and (ldd or lightly-doped or lightly adj doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:49
-	0	cold adj cathode and field adj emission and extract\$3 near4 gate and source and drain and channel and silicon near4 substrate and (ldd or lightly-doped or lightly adj doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:49
-	13	(cold near2 cathode or field adj emission adj cathode) and gate and source and drain and channel and silicon near4 substrate and (ldd or lightly-doped or lightly adj doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:53
-	2	("5550435").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:59
-	6952	lightly adj doped adj drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:02

-	2155	lightly adj doped adj drain.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:15
-	0	lightly adj doped adj drain.ti,ab. and cold adj cathode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:03
-	0	lightly adj doped adj drain.ti,ab. and field adj emission adj cathode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:04
-	0	(ldd or lightly-doped adj drain or lightly adj doped adj drain) and (cold adj cathode or field adj emission adj cathode).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:08
-	0	jp-6055616\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:11
-	2	jp-60055616\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:11
-	1	lightly adj doped adj drain.ti,ab. and phosphorus near10 arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:17
-	0	lightly adj doped adj drain near10 phosphorus near10 arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:17
-	0	(ldd or lightly adj doped adj drain) near10 phosphorus near10 arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:18
-	1	(ldd or lightly adj doped adj drain) and phosphorus near10 arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:27
-	2	("5550435").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 14:07
-	1750	ldd and phosphorus same arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 14:08
-	16	ldd and phosphorus same arsenic same different near3 diffusion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 14:09
-	0	cold adj cathode and (field adj effect adj transistor or fet) and (gate near4 different near4 width)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 14:58

-	200	(field adj effect adj transistor or fet) and (gate near4 different near4 width)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 14:59
-	2	(field adj effect adj transistor or fet) and (gate near4 different near4 width) and (hot near3 electron) and (ldd or lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:00
-	10	(field adj effect adj transistor or fet) and (gate near4 different near4 width) and (hot near3 electron)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:01
-	1068	width near6 gate near6 (variable or different)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:08
-	137	width near6 gate near6 (variable or different) and 257/\$6.ccls. and (ldd or lightly-doped drain or lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:09
-	90	width near3 gate near3 (variable or different) and 257/\$6.ccls. and (ldd or lightly-doped drain or lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:11
-	27	width near3 gate near3 (variable or different) and 257/\$6.ccls. and (ldd or lightly-doped drain or lightly adj doped adj drain) and plan adj view	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:19
-	329	257/249.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:24
-	6	257/249.ccls. and (ldd or lightly adj doped adj drain or lightly-doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:21
-	15	257/249.ccls. and gate adj width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:29
-	114	257/401.ccls. and gate adj width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:36
-	13	257/401.ccls. and gate near3 (width or wider) near4 source near4 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:43
-	2	jp-60022375\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 16:37
-	2	("5550435").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 16:55

-	1002	shield\$3 near4 gate near4 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 16:56
-	3849	shield\$3 adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 16:56
-	556	shield\$3 adj electrode and (257/\$6.ccls. or 313/\$6.ccls. or 315/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 16:57
-	3	shield adj electrode near10 gate and (257/\$6.ccls. or 313/\$6.ccls. or 315/\$6.ccls.) and (cold adj cathode or field adj emission)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 17:31
-	697	(electrode near3 (shield or shielding) near3 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 17:38
-	398	(electrode near3 (shield or shielding) near3 gate) and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 18:26
-	0	(electrode near3 (shield or shielding) near3 gate) and channel and flat adj type adj display	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 18:27
-	13	(electrode near3 (shield or shielding) near3 gate) and channel and flat adj2 display	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 19:57
-	0	jp-0963467\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 20:53
-	2	((("5550435") or ("5396096"))).PN.	USPAT	2002/05/19 21:09
-	2	jp-62229880\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 21:18
-	0	jp-64061953\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 21:18
-	0	jp-6461953\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 21:18
-	4003	((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/249) or (257/401) or (257/146) or (257/153)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 21:55

-	12	((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/249) or (257/401) or (257/146) or (257/153)).CCLS.) and shield near3 electrode near3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 21:38
-	238	(257/10).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 22:06
-	0	(257/10 and shield\$3).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 22:07
-	18	((257/10).CCLS.) and shield\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 22:07
-	13	drain near3 p-type near4 n-type same (punch adj through or punch-through)	USPAT	2002/05/20 08:11
-	50	(US-6340859-\$ or US-5396096-\$ or US-6218771-\$ or US-6031322-\$ or US-6084341-\$ or US-6031250-\$ or US-5910701-\$ or US-5864147-\$ or US-5844252-\$ or US-6140687-\$ or US-5550426-\$ or US-5898198-\$ or US-5319233-\$ or US-5285079-\$ or US-6369505-\$ or US-6369496-\$ or US-6356014-\$ or US-6351059-\$ or US-5347292-\$ or US-5229331-\$ or US-5191217-\$ or US-5142184-\$ or US-6211608-\$ or US-6140701-\$ or US-6181060-\$ or US-6075315-\$).did. or (US-5633560-\$ or US-5055077-\$ or US-5012482-\$ or US-5007873-\$ or US-5920296-\$ or US-6020595-\$ or US-5500572-\$ or US-5212426-\$ or US-6340962-\$ or US-5214346-\$ or US-5918137-\$ or US-5461242-\$ or US-4742380-\$ or US-6028322-\$ or US-5965898-\$ or US-4968639-\$).did. or (JP-09063467-\$ or JP-09259746-\$ or JP-09035622-\$ or JP-10074473-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-62229880-\$).did. or (EP-651417-\$).did.	USPAT; JPO; DERWENT	2002/10/24 18:07
-	2	(lightly-doped adj drain or lightly adj doped adj drain or ldd) near6 surround\$3 near6 (heavily-doped adj drain or heavily adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 18:10

-	50	(US-6020595-\$ or US-5920296-\$ or US-5500572-\$ or US-5212426-\$ or US-6340859-\$ or US-6218771-\$ or US-6140701-\$ or US-6084341-\$ or US-6031322-\$ or US-6031250-\$ or US-5910701-\$ or US-5864147-\$ or US-5844252-\$ or US-5550426-\$ or US-5319233-\$ or US-5285079-\$ or US-6369505-\$ or US-6369496-\$ or US-6356014-\$ or US-6351059-\$ or US-6211608-\$ or US-6181060-\$ or US-6075315-\$ or US-5633560-\$ or US-5347292-\$ or US-5229331-\$).did. or (US-5191217-\$ or US-5142184-\$ or US-5055077-\$ or US-5012482-\$ or US-5007873-\$ or US-5396096-\$ or US-6140687-\$ or US-5898198-\$ or US-6340962-\$ or US-5214346-\$ or US-5918137-\$ or US-5461242-\$ or US-4742380-\$ or US-6028322-\$ or US-5965898-\$ or US-4968639-\$).did. or (JP-09259746-\$ or JP-11102637-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-09035622-\$ or JP-10074473-\$ or JP-62229880-\$).did. or (EP-651417-\$).did.	USPAT; JPO; DERWENT	2002/10/25 09:24
-	0	ogata.in. and gate adj electrode and field adj emission	JPO	2002/10/25 09:26
-	72	ogata.in. and gate adj electrode	JPO	2002/10/25 11:00
-	302	(mos or mosfet or cmosfet or cmos or nmos or nmosfet or pmosfet or pmos).ti,ab,clm. and (width or wide or wider) near6 gate near6 drain near6 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 11:03
-	70	(mos or mosfet or cmosfet or cmos or nmos or nmosfet or pmosfet or pmos).ti,ab,clm. and (width or wide or wider) near3 gate near3 drain near3 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 11:03
-	1	(mos or mosfet or cmosfet or cmos or nmos or nmosfet or pmosfet or pmos).ti,ab,clm. and wider near3 gate near3 drain near3 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 11:56
-	2	jp-09063467\$-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 11:56
-	2765	((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/146) or (257/153)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:56
-	163	((((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/146) or (257/153)).CCLS.) and (field adj emission or field-emission) near3 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:56
-	97	((((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/146) or (257/153)).CCLS.) and (field adj emission or field-emission) near3 source) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:59
-	4	(((((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/146) or (257/153)).CCLS.) and (field adj emission or field-emission) near3 source) and gate) and electrode near6 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 14:18

-	2	("5965921").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 14:18
-	3934	((257/10) or (257/249) or (257/401) or (315/167) or (315/169.1) or (315/169.2) or (315/309) or (313/336)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/19 17:17
-	6	((257/10) or (257/249) or (257/401) or (315/167) or (315/169.1) or (315/169.2) or (315/309) or (313/336)).CCLS.) and shielding adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/19 17:19
-	2	("5965921").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/19 17:19
-	52	(US-5142184-\$ or US-5012482-\$ or US-5055077-\$ or US-5007873-\$ or US-5396096-\$ or US-6140687-\$ or US-5898198-\$ or US-6028322-\$ or US-4968639-\$ or US-6369505-\$ or US-6351059-\$ or US-5918137-\$ or US-5285079-\$ or US-5461242-\$ or US-5319233-\$ or US-6340962-\$ or US-5847408-\$ or US-6340859-\$ or US-6140701-\$ or US-6218771-\$ or US-6084341-\$ or US-6031322-\$ or US-6031250-\$ or US-5910701-\$ or US-5864147-\$ or US-5844252-\$).did. or (US-5550426-\$ or US-6369496-\$ or US-6356014-\$ or US-6211608-\$ or US-6181060-\$ or US-6075315-\$ or US-5633560-\$ or US-5347292-\$ or US-5229331-\$ or US-5191217-\$ or US-5214346-\$ or US-5965898-\$ or US-4742380-\$ or US-5920296-\$ or US-6020595-\$ or US-5500572-\$ or US-5212426-\$).did. or (JP-01061953-\$ or JP-09063467-\$ or JP-09259746-\$ or JP-09063466-\$ or JP-09035622-\$ or JP-62229880-\$ or JP-10074473-\$ or JP-11102637-\$).did. or (EP-651417-\$).did.	USPAT; JPO; DERWENT	2003/04/23 15:59
-	4045	((257/209) or (257/401) or (257/10) or (315/167) or (315/169.1) or (315/169.2) or (315/309) or (313/336)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/23 16:02
-	108	((257/209) or (257/401) or (257/10) or (315/167) or (315/169.1) or (315/169.2) or (315/309) or (313/336)).CCLS.) and gate near20 extraction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/23 16:20
-	2	("5550435").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/23 17:06
-	2	("5965921").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/23 17:08
-	2	jp-01061953\$-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/23 18:34

-	2	jp-09063467\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/23 18:34
-	2	("5233215").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/24 11:08
-	54	(US-5191217-\$ or US-5229331-\$ or US-5347292-\$ or US-5633560-\$ or US-5007873-\$ or US-5012482-\$ or US-5055077-\$ or US-5142184-\$ or US-5864147-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6140701-\$ or US-6218771-\$ or US-6340859-\$ or US-5212426-\$ or US-5500572-\$ or US-5920296-\$ or US-6020595-\$ or US-5965898-\$ or US-5898198-\$ or US-5847408-\$ or US-6140687-\$ or US-5396096-\$ or US-6028322-\$).did. or (US-4742380-\$ or US-5461242-\$ or US-5918137-\$ or US-5214346-\$ or US-6340962-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5233215-\$ or US-5965921-\$ or US-4968639-\$).did. or (JP-11102637-\$ or JP-10074473-\$ or JP-09035622-\$ or JP-09063466-\$ or JP-09259746-\$ or JP-09063467-\$ or JP-62229880-\$ or JP-01061953-\$).did. or (EP-651417-\$).did.	USPAT; JPO; DERWENT	2003/04/24 11:27
-	2	jp-09063467\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/24 18:10